SOT323 PNP SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

ZUMT591

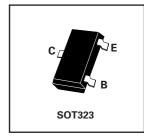
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FFATURES

- * Extremely low saturation voltage
- * 500mW power dissipation
- * 1 Amp continuous collector current (I_C)

APPLICATIONS

* Ideally suited for space / weight critical applications



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current	I _{CM}	-2	Α
Continuous Collector Current	I _c	-1	Α
Base Current	I _B	-200	mA
Power Dissipation at T _{amb} =25°C	P _{tot}	500	mW
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80			V	I _C =-100μA, I _E =-0
Collector-Emitter Breakdown Voltage	V _{CEO(sus)}	-60			V	I _C =-10mA*, I _B =-0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5			V	I _E =-100μA, I _C =-0
Collector Cut-Off Current	I _{CBO}			-100	nA	V _{CB} =-60V
Collector Cut-Off Current	I _{CES}			-100	nA	VCE=-60V
Emitter Cut-Off Current	I _{EBO}			-100	nA	V _{EB} =-4V, I _C =-0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.3 -0.6	V	I _C =-500mA, I _B =-50mA* I _C =-1A, I _B =-100mA*
Base-Emitter Saturation Voltage	V _{BE(sat)}			-1.2	V	I _C =-1A, I _B =-100mA*
Base-Emitter Turn On Voltage	V _{BE(on)}			-1.0	V	IC=-1A, V _{CE} =-5V*

^{*} Measured under pulsed conditions. Pulse width=300µs. Duty cycle@2%

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ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Static Forward Current Transfer Ratio	h _{FE}	100 100 80 15		300		I _C =-1mA, V _{CE} =-5V* I _C =-500mA, V _{CE} =-5V* I _C =-1A, V _{CE} =-5V* I _C =-2A, V _{CE} =-5V*
Transition Frequency	f _T	150			MHz	I _C =-50mA, V _{CE} =-10V* f=100MHz
Ouput Capacitance	C _{obo}			10	pF	V _{CB} =-10V, f=1MHz

^{*} Measured under pulsed conditions. Pulse width=300µs. Duty cycle @2%

NOTE

This data is derived from development material and does not necessarily mean that the device will go into production

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